

L Number	Hits	Search Text	DB	Time stamp
1	104	trench adj isolation	IBM_TDB	2003/12/17 14:55
2	28	(trench adj isolation) same lining	EPO; JPO; DERWENT	2003/12/17 15:02
9	3	("5498565" "5578518" "5665635").PN.	USPAT	2003/12/17 15:05
12	11	("4546538" "4631803" "4666556" "4719185" "4855804" "4983226" "5183774" "5189501" "5206182" "5250829" "5271972").PN.	USPAT	2003/12/17 15:06
13	70	5447884.URPN.	USPAT	2003/12/17 15:07
-	573	(257/324,326).CCLS.	USPAT; US-PGPUB	2003/12/17 14:12
-	44	((257/324,326).CCLS.) and @pd>20030708	USPAT; US-PGPUB	2003/12/17 14:14
-	1	("6495853").PN.	USPAT; US-PGPUB	2003/12/17 14:15
-	6	("6087696" "6093606" "6118147" "6177317" "6232635" "6255689").PN.	USPAT	2003/12/17 14:14
-	9934	trench adj isolation	USPAT; US-PGPUB	2003/12/17 14:15
-	75	(trench adj isolation) same lining	USPAT; US-PGPUB	2003/12/17 15:02
-	9	("5231299" "5447884" "5597751" "5652161" "5851881" "6017795" "6074927" "6093611" "6110800").PN.	USPAT	2003/12/17 14:24

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 6630390 B2	8	Method of forming a semiconductor device using a carbon doped oxide layer to control the chemical mechanical polishing of a dielectric layer	438/427	438/435; 438/637; 438/692	Andideh, Ebrahim et al.
2	US 5926722 A	8	Planarization of shallow trench isolation by differential etchback and chemical mechanical polishing	438/424	257/E21.244; 257/E21.246; 257/E21.251; 257/E21.546; 438/692; 438/734; 438/743; 438/756	Jang, S. M. et al.
3	US 5786262 A	9	Self-planarized gapfilling for shallow trench isolation	438/424	148/DIG.50; 257/E21.279; 257/E21.546; 438/221; 438/296; 438/427; 438/435; 438/437	Jang, S. M. et al.
4	US 5447884 A	4	Shallow trench isolation with thin nitride liner	438/437	148/DIG.50; 257/E21.241; 257/E21.549; 438/702	Fahey, Paul M. et al.
5	US 4924284 A	8	Method of trench filling	257/621	257/508; 257/513; 257/519; 257/520; 257/648; 257/E21.149; 257/E21.538; 257/E21.572	Beyer, Klaus D. et al.